

500mA 20V Low VF(0.79x0.65mm)

Chip Information

Chip Size	0.79 x 0.65mm
Pad Size	0.66 x 0.52mm
Chip Quantity	21362 pcs/wafer
Scribe Line Width	50um
Passivation	PSG
Wafer Size	5 inch
Top Metallization	Al(For Wire)

Chip Thickness/Back Metal : See below "Ordering Information"

MAXIMUM RATINGS

Parameter	Symbol	Limit	Unit	Note
Repetitive Peak Reverse Voltage	VRRM	20	V	
Non-Repetitive Peak Reverse Voltage	VRSM		V	
Maximum DC Blocking Voltage	VR	20	V	
Average Forward Rectified Current	IF(AV)	500	mA	
Peak Forward Surge Current	IFSM	5.5	A	8.3ms Single Half Sine-Wave
Storage and Operating Temperature Range	Tj,TSTG	-65 to +125	degC	

ELECTRICAL CHARACTERISTICS

Parameter	Symbol	Spec Limit	Probe Spec	Typical	Unit	Test Condition
Maximum Forward Voltage	VF1	0.385	0.365	0.350	V	IF=500mA Ta=25degC
	VF2	0.300	0.280	0.260	V	IF=100mA Ta=25degC
	VF3	0.330		0.285	V	IF=500mA Ta=100degC
	VF4	0.220		0.168	V	IF=100mA Ta=100degC
	VF5				V	
Maximum DC Reverse Current	IR1	75	60	26	uA	VR=10V Ta=25degC
	IR2	250	150	44	uA	VR=20V Ta=25degC
	IR3			2800	uA	VR=10V Ta=100degC
	IR4			5600	uA	VR=20V Ta=100degC
Reverse Breakdown Voltage	BV	20	25	45	V	IR=250uA
Junction Capacitance	Cj	170		120	pF	VR=0V,f=1MHz
Reverse Recovery Time	trr				nS	IF=IR=10mA irr=0.1IR

Ordering Information

Chip Type	Chip Thickness	Back Metal
YCF115	180 +/- 20um	Au(For Eutectic)
YCF117	150 +/- 20um	Au(For Eutectic)
YCF116	180 +/- 20um	Ti-Ni-Ag(For Ag Epoxy)

Note:
Designed For MBR0520L